

Dual N-Channel Enhancement Mode MOSFET

Feature

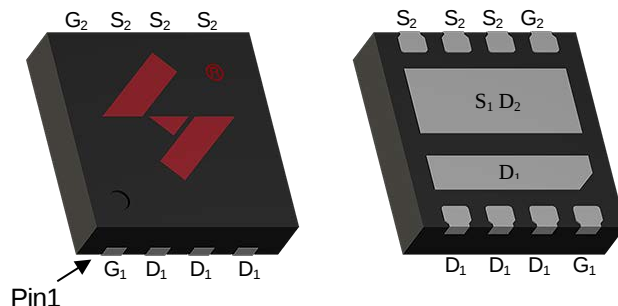
	Q1	Q2
V_{DS}	30V	30V
I_D ($V_{GS} = 10V$)	31A	33A
$R_{DS(ON)}$ (typ) @ $V_{GS} = 10V$	8.8 mR	7.3 mR
$R_{DS(ON)}$ (typ) @ $V_{GS} = 4.5V$	12.4 mR	10.3 mR

- 100% Avalanche Tested
- Reliable and Rugged
- Halogen- Free Devices Available

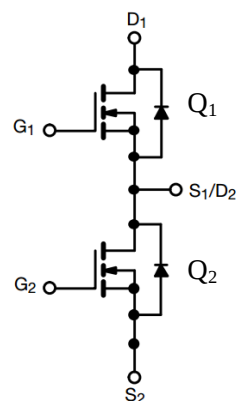
Applications

- Synchronous Rectifiers
- Wireless Power
- H-bridge Motor Drive

Pin Description



DFN3*3-8L



Dual N-Channel MOSFET

Ordering and Marking Information

 C1 G080NH03 XYMXXXXXX	Package Code C1: DFN3*3-8L Date Code XYMXXXXXX
---	---

Note: HUAYI lead-free products contain molding compounds/die attach materials and 100% matte tin plate Termination finish; which are fully compliant with RoHS. HUAYI lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020 for MSL classification at lead-free peak reflow temperature. HUAYI defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

HUAYI reserves the right to make changes, corrections, enhancements, modifications, and improvements to this product and/or to this document at any time without notice.

Absolute Maximum Ratings

Symbol	Parameter		MAX Q1	MAX Q2	Unit
	Common Ratings (Tc=25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		30		V
V _{GSS}	Gate-Source Voltage		±20		V
T _J	Maximum Junction Temperature		-55 to 175		°C
T _{STG}	Storage Temperature Range		-55 to 175		°C
I _S	Source Current-Continuous(Body Diode)	Tc=25°C	31	33	A
	Mounted on Large Heat Sink				
I _{DM}	Pulsed Drain Current *	Tc=25°C	111	118	A
I _D	Continuous Drain Current	Tc=25°C	31	33	A
		Tc=100°C	22	23	A
P _D	Maximum Power Dissipation	Tc=25°C	21.4		W
		Tc=100°C	10.7		W
R _{θJC}	Thermal Resistance, Junction-to-Case		7		°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient **		75		°C/W
E _{AS}	SinglePulsed-Avalanche Energy ***	L=0.1mH	22.9	34.3	mJ

Note: * Repetitive rating; pulse width limited by max.junction temperature.

** Surface mounted on 1in2 FR-4 board.

*** Limited by T_{Jmax}, starting T_J=25°C, L = 0.1mH, R_C= 25Ω, V_{GS}=10V.

Q1 Electrical Characteristics (T_c =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Q1			Unit
			Min	Typ.	Max	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30	-	-	V
I _{DSS}	Drain-to-Source Leakage Current	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
		T _j =125°C	-		50	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1	1.6	3	V
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} *	Drain-Source On-State Resistance	V _{GS} =10V, I _{DS} = 10 A	-	8.8	11	mΩ
		V _{GS} =4.5V, I _{DS} = 10A		12.4	15	mΩ
Diode Characteristics						
V _{SD} *	Diode Forward Voltage	I _{SD} =1A, V _{GS} =0V	-	0.7	1.0	V
t _{rr}	Reverse Recovery Time	I _{SD} =10A, dI _{SD} /dt=100A/μs	-	8.2	-	ns
Q _{rr}	Reverse Recovery Charge		-	3.1	-	nC

Q1 Electrical Characteristics (Cont.) (T_c =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Q1			Unit
			Min	Typ.	Max	
Dynamic Characteristics						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz	-	1.2	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V,	-	709.1	-	pF
C _{oss}	Output Capacitance	V _{DS} =25V,	-	87	-	
C _{rss}	Reverse Transfer Capacitance	Frequency=1.0MHz	-	70.7	-	
t _d (ON)	Turn-on Delay Time	V _{DD} =10V,R _G =2.7Ω, I _{DS} =4A,V _{GS} =10V	-	5.8	-	ns
T _r	Turn-on Rise Time		-	14.5	-	
t _d (OFF)	Turn-off Delay Time		-	15.6	-	
T _f	Turn-off Fall Time		-	3.4	-	
Gate Charge Characteristics						
Q _g	Total Gate Charge (V _{GS} =10V)	V _{DS} =15V, I _D =10A		16		nC
Q _g	Total Gate Charge (V _{GS} =4.5V)		-	7.8	-	
Q _{gs}	Gate-Source Charge		-	2.9	-	
Q _{gd}	Gate-Drain Charge		-	3.3	-	

Note: *Pulse test, pulse width ≤ 300us, duty cycle ≤ 2%

Q1-Channel Typical Operating Characteristics

Figure 1: Power Dissipation

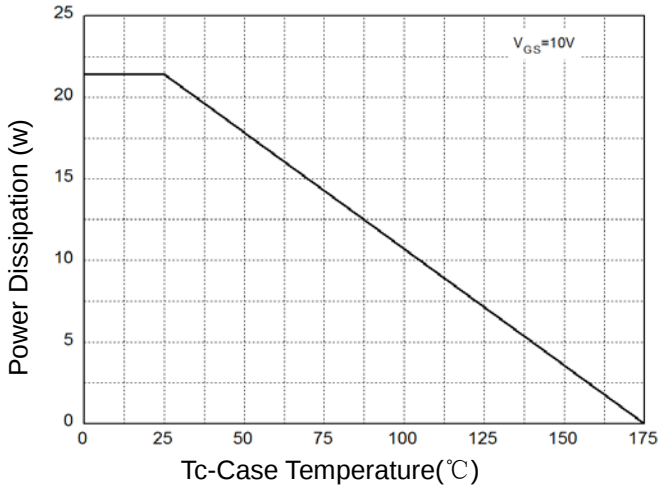


Figure 2: Drain Current

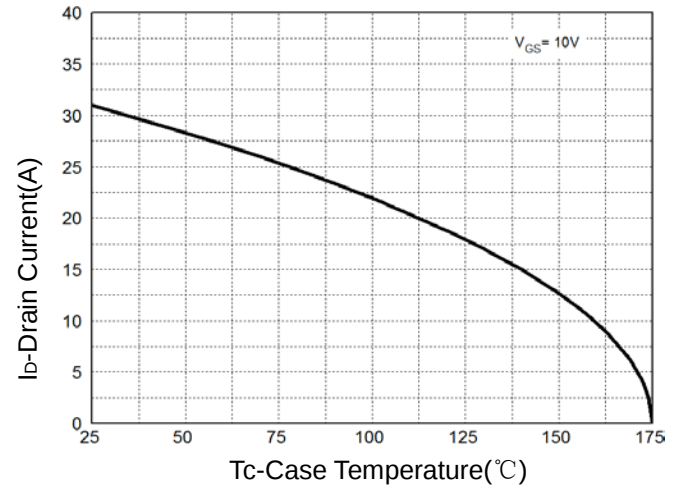


Figure 3: Safe Operation Area

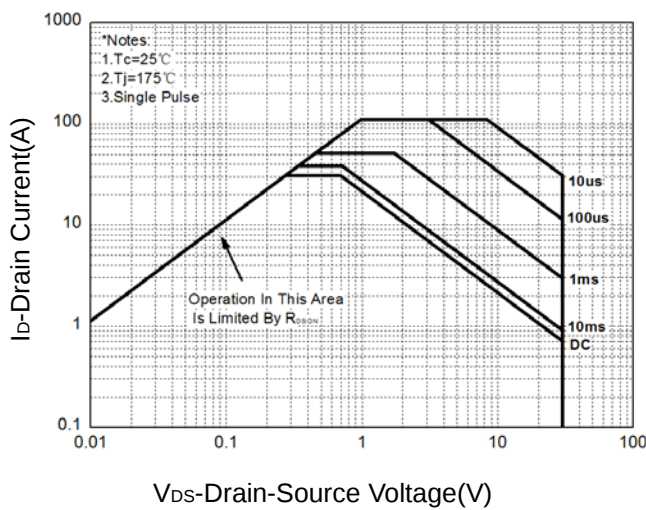


Figure 4: Thermal Transient Impedance

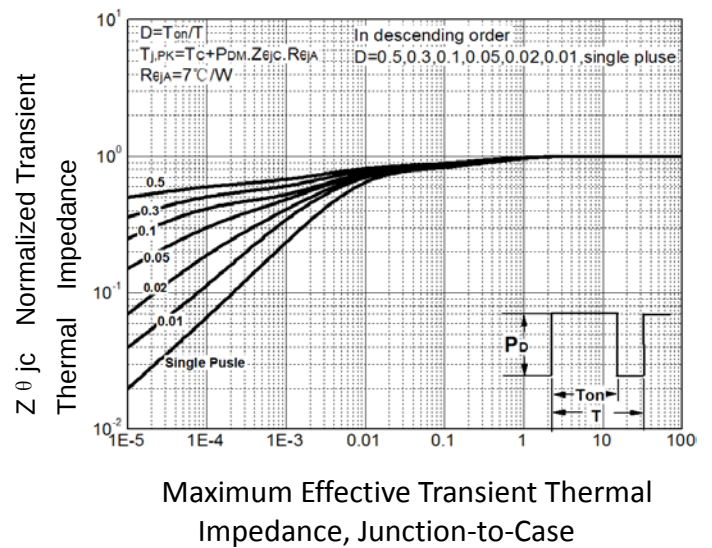


Figure 5: Output Characteristics

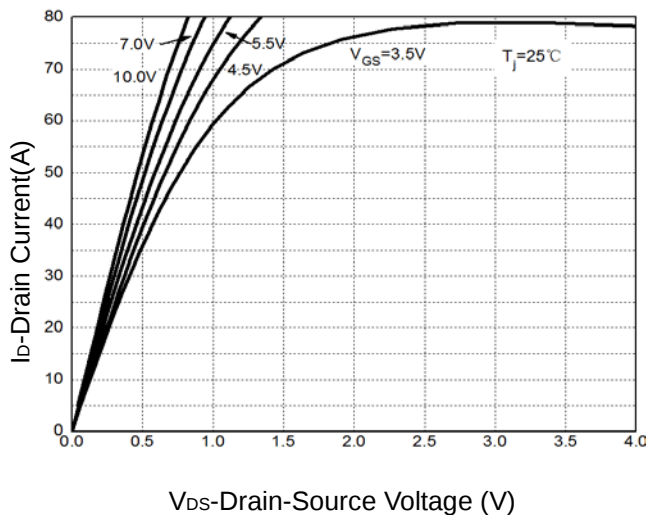
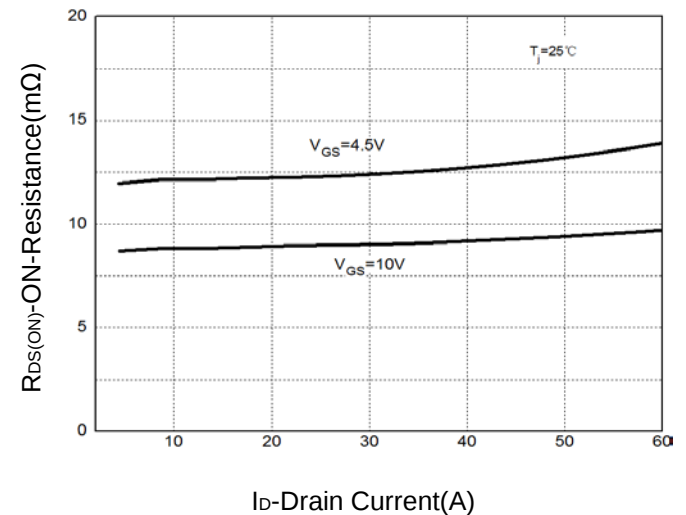


Figure 6: Drain-Source On Resistance



Q1-Channel Typical Operating Characteristics(Cont.)

Figure 7: On-Resistance vs. Temperature

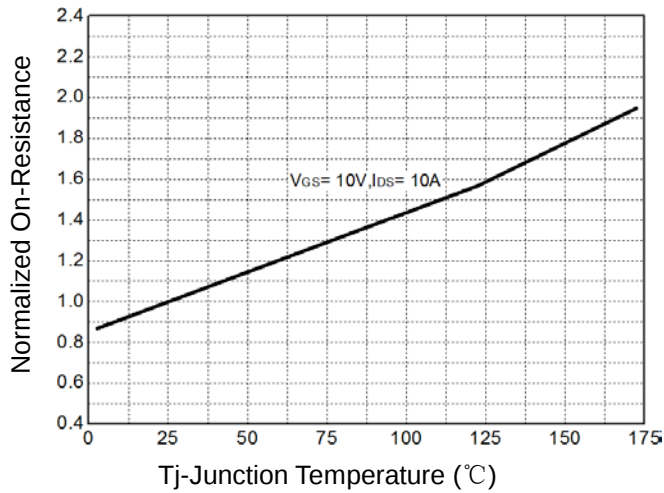


Figure 8: Source-Drain Diode Forward

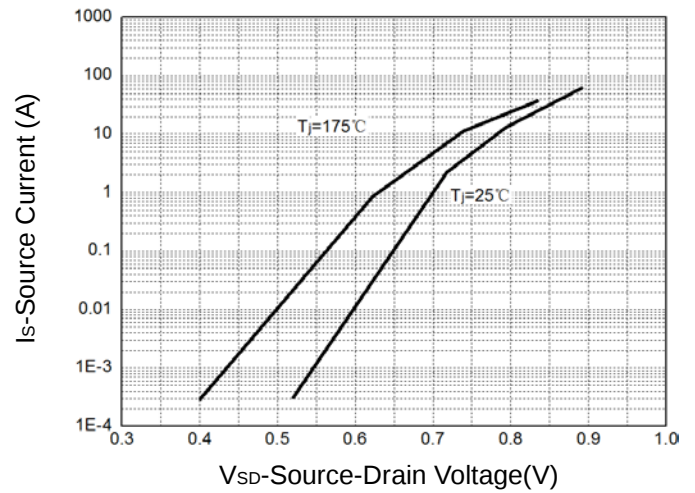


Figure 9: Capacitance Characteristics

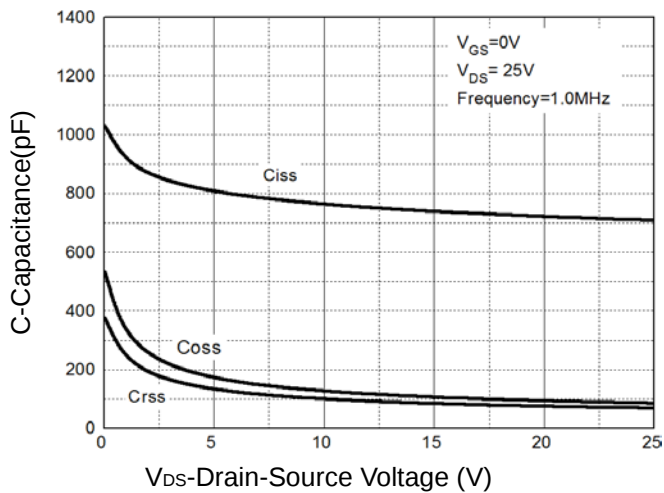
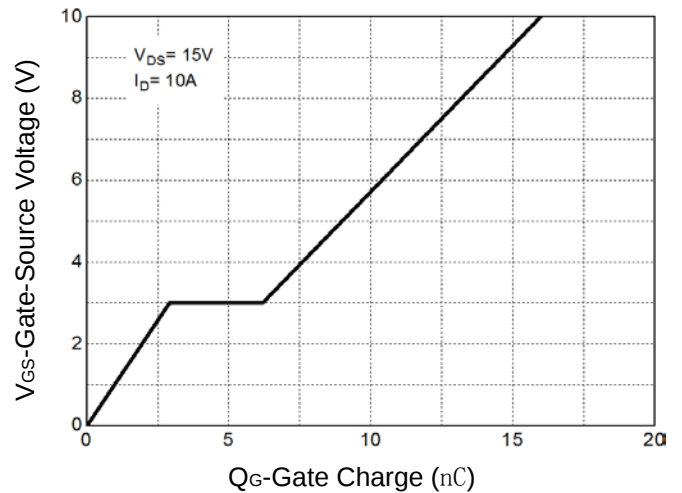


Figure 10: Gate Charge Characteristics



Q2 Electrical Characteristics ($T_c = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions		Q2			Unit
				Min	Typ.	Max	
Static Characteristics							
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA		30	-	-	V
I _{DSS}	Drain-to-Source Leakage Current	V _{DS} =30V, V _{GS} =0V		-	-	1	μA
			T _J =125°C	-		50	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA		1	1.7	3	V
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0V		-	-	±100	nA
R _{DS(ON)} *	Drain-Source On-State Resistance	V _{GS} =10V, I _{DS} =10A		-	7.3	9.5	mΩ
		V _{GS} =4.5V, I _{DS} =10A			10.3	12.5	mΩ
Diode Characteristics							
V _{SD} *	Diode Forward Voltage	I _{SD} =1A, V _{GS} =0V		-	0.7	1.0	V
t _{rr}	Reverse Recovery Time	I _{SD} =10A, dI _{SD} /dt=100A/μs		-	10	-	ns
Q _{rr}	Reverse Recovery Charge			-	4.4	-	nC

Q2 Electrical Characteristics (Cont.) ($T_c = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Q2			Unit
			Min	Typ.	Max	
Dynamic Characteristics						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz	-	1.0	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V,	-	966	-	pF
C _{oss}	Output Capacitance	V _{DS} =25V,	-	117	-	
C _{rss}	Reverse Transfer Capacitance	Frequency=1.0MHz	-	101	-	
t _d (ON)	Turn-on Delay Time	V _{DD} =10V,R _G =2.7Ω, I _{DS} =4A,V _{GS} =10V	-	6.8	-	ns
T _r	Turn-on Rise Time		-	16.6	-	
t _d (OFF)	Turn-off Delay Time		-	19.4	-	
T _f	Turn-off Fall Time		-	5.4	-	
Gate Charge Characteristics						
Q _g	Total Gate Charge (V _{GS} =10V)	V _{DS} =15V,I _D =10A		23.2		nC
Q _g	Total Gate Charge (V _{GS} =4.5V)		-	11.8	-	
Q _{gs}	Gate-Source Charge		-	4.0	-	
Q _{gd}	Gate-Drain Charge		-	5.0	-	

Note: *Pulse test, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

Q2-Channel Typical Operating Characteristics

Figure 1: Power Dissipation

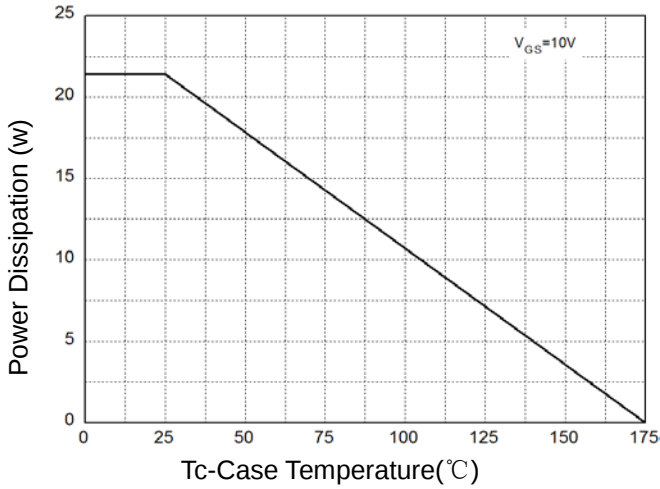


Figure 2: Drain Current

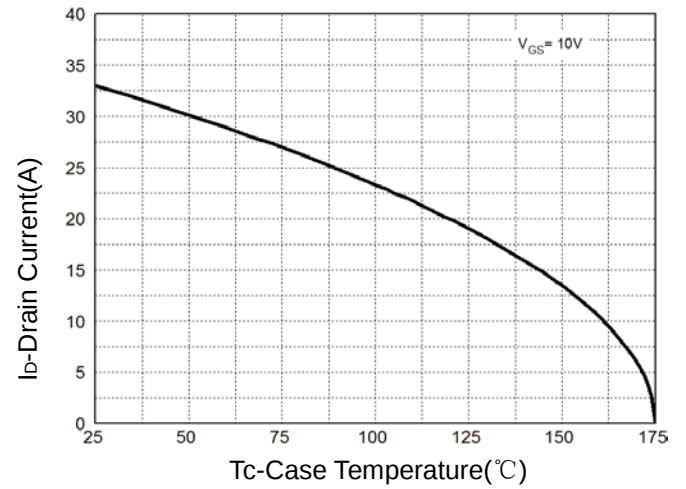


Figure 3: Safe Operation Area

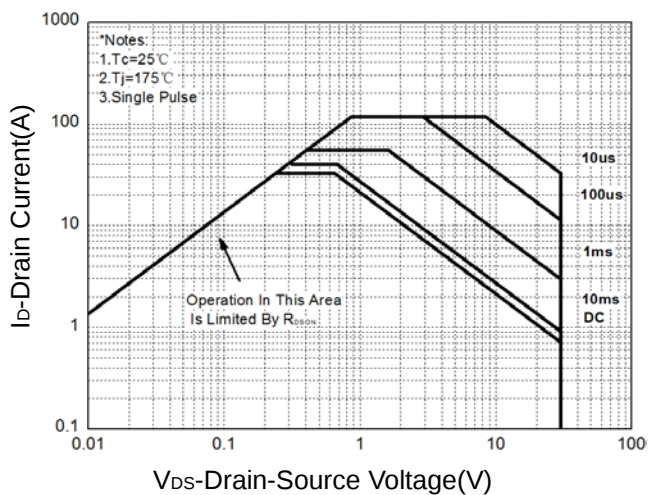


Figure 4: Thermal Transient Impedance

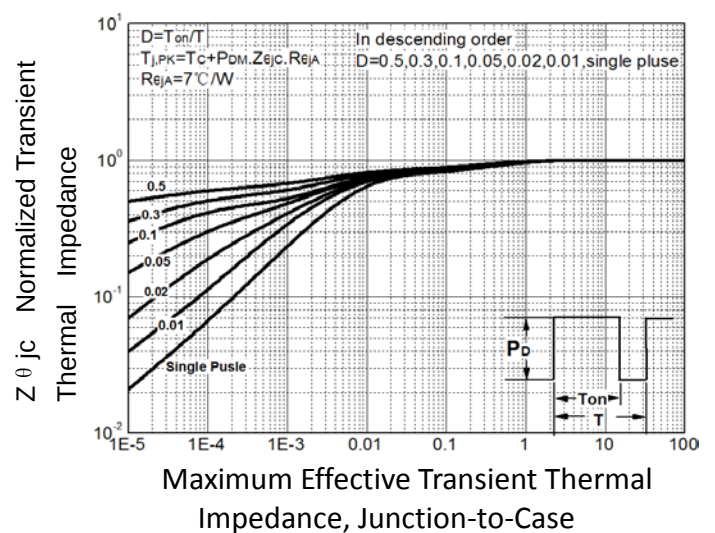


Figure 5: Output Characteristics

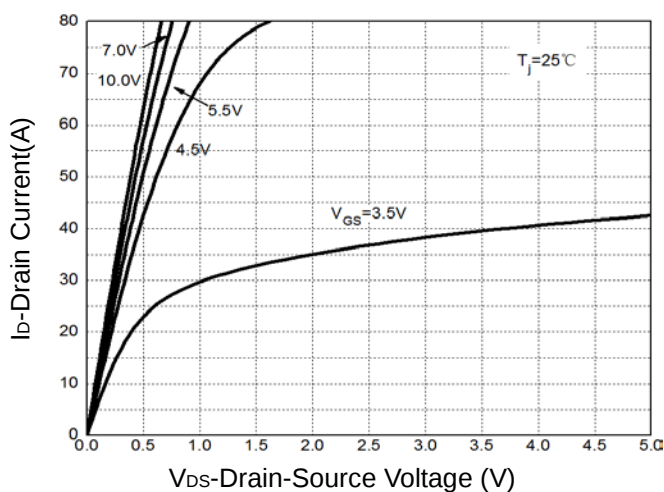
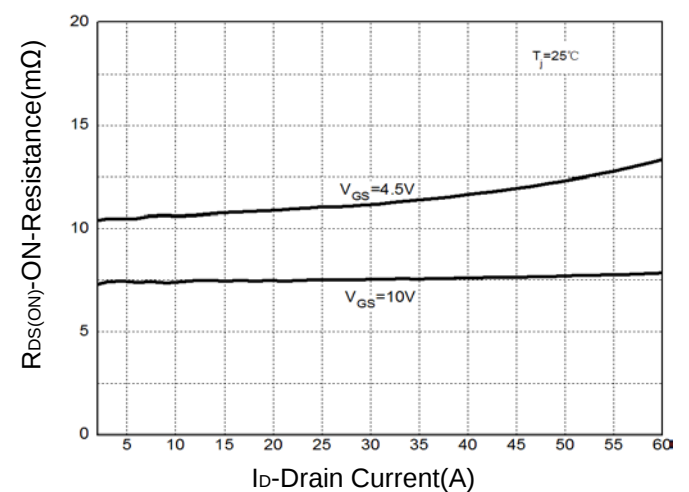


Figure 6: Drain-Source On Resistance



Q2-Channel Typical Operating Characteristics(Cont.)

Figure 7: On-Resistance vs. Temperature

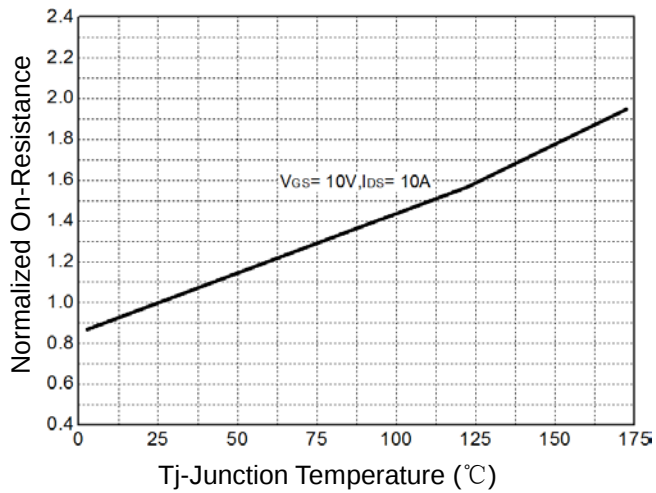


Figure 8: Source-Drain Diode Forward

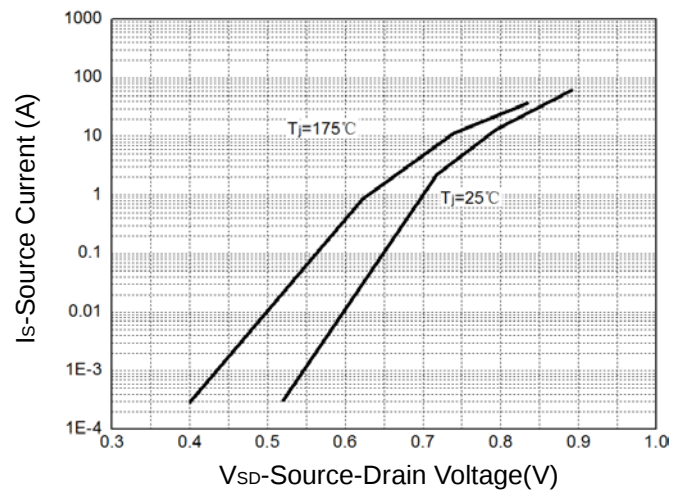


Figure 9: Capacitance Characteristics

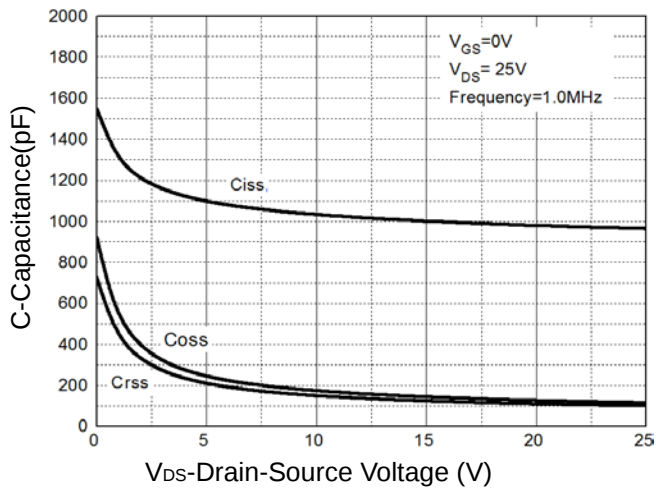
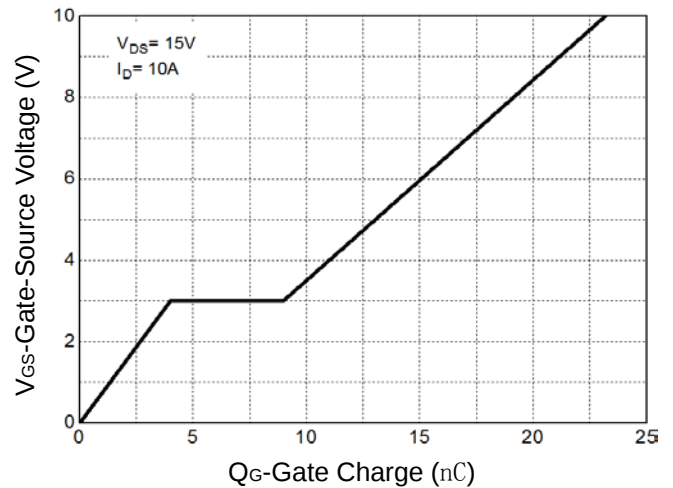
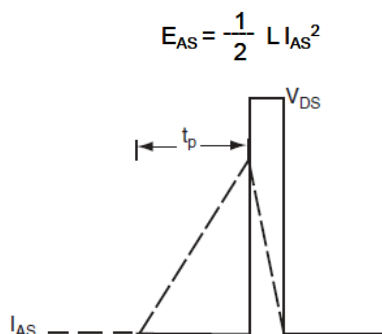
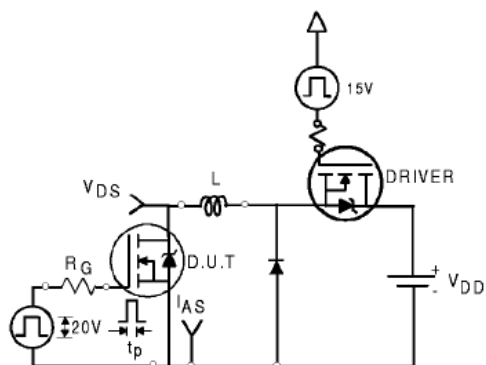


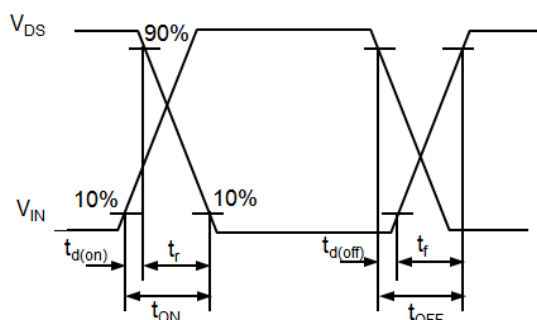
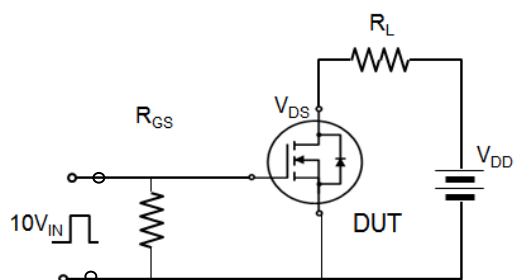
Figure 10: Gate Charge Characteristics



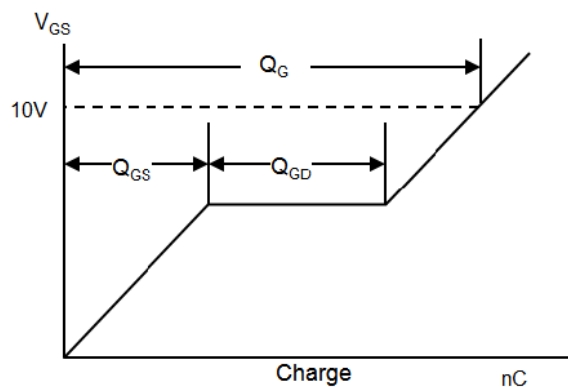
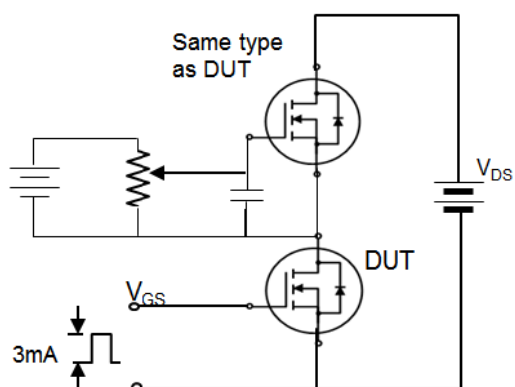
Avalanche Test Circuit



Switching Time Test Circuit



Gate Charge Test Circuit

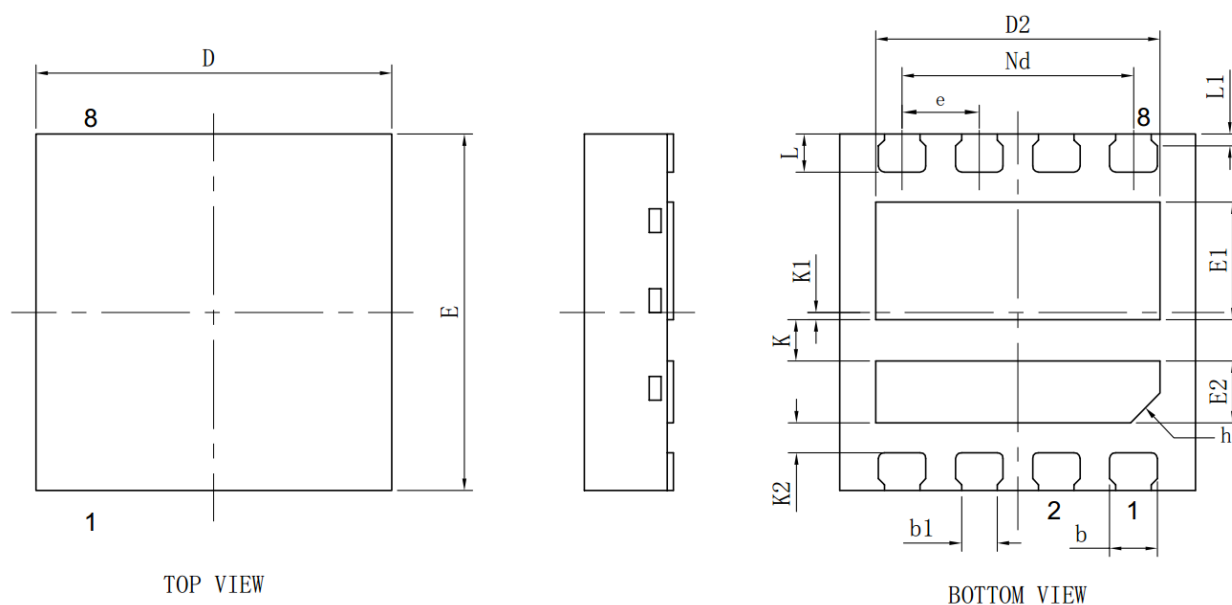


Device Per Unit

Package Type	Unit	Quantity
DFN3*3-8L	Reel	6500

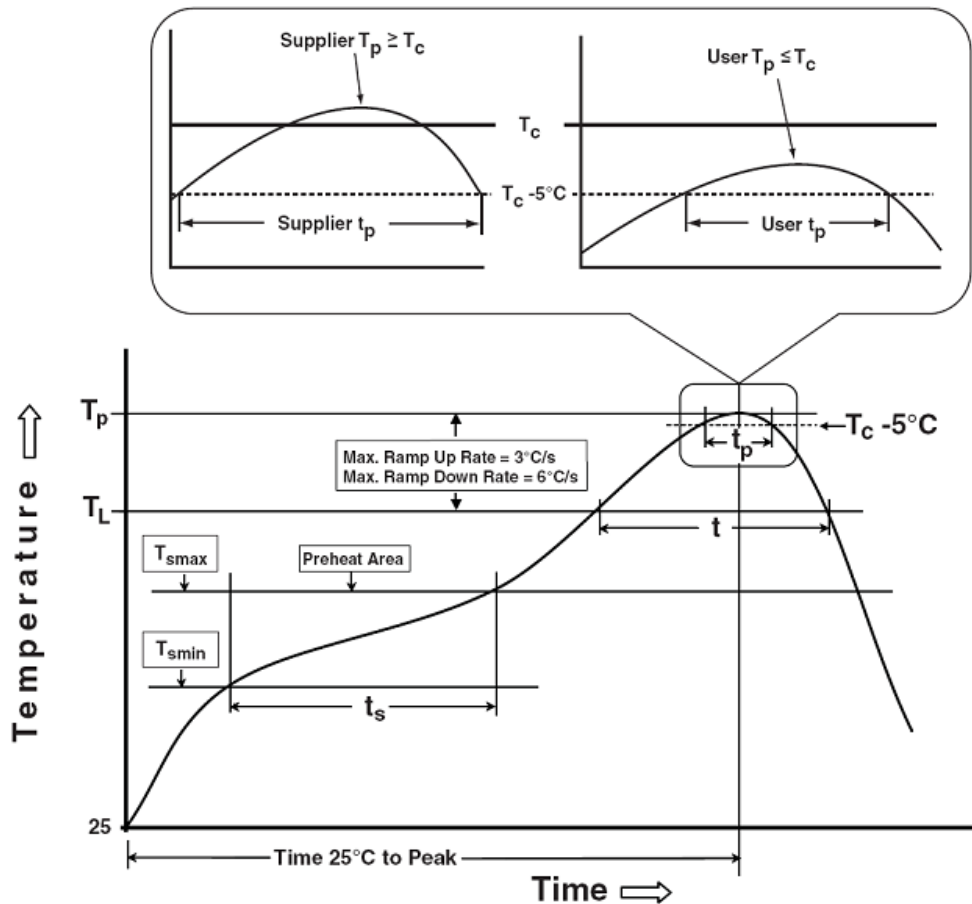
Package Information

DFN3*3-8L



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
b	0.35	0.40	0.45
b1	0.30REF		
c	0.18	0.20	0.25
D	2.90	3.00	3.10
D2	2.30	2.40	2.50
Nd	1.90	1.95	2.00
E	2.90	3.00	3.10
E1	0.89	0.99	1.09
E2	0.42	0.52	0.62
e	0.65BSC		
K	0.35REF		
K1	0.06REF		
K2	0.25REF		
L	0.27	0.32	0.37
L1	0.10REF		
h	0.20	0.25	0.30

Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
*Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1.SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm³ <350	Volume mm³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2.Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm³ <350	Volume mm³ 350-2000	Volume mm³ ≥2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	168Hrs/500Hrs/1000Hrs, Bias @ 150°C
PCT	JESD-22, A102	96 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -55°C~150°C

Customer Service

Worldwide Sales and Service: sales@hymexa.com

Technical Support: Technology@hymexa.com

Huayi Microelectronics Co., Ltd.

No.8928,Shangji Road,Economic and Technological Development Zone,Xi'an,China

TEL: (86-029) 86685706

FAX: (86-029) 86685705

E-mail: sales@hymexa.com

Web net: www.hymexa.com